NSN 5961-01-135-2073

Transistor - Page 1 of 2

ACTOBAS Grou

View Online at https://aerobasegroup.com/nsn/5961-01-135-2073

Inclosure Material:

Metal

Overall Length:

1.573 inches

Overall Height:

Between 0.250 inches and 0.450 inches

Overall Width:

1.050 inches

End Application:

1270-01-122-5234 18876

Mounting Facility Quantity:

2

Internal Configuration:

Junction contact

Joint Electronic Device Engineering Council/jedec/case Outline Designation:

To-3

Electrode Internally-electrically Connected To Case:

Collector

Mounting Method:

Unthreaded hole

Features Provided:

Hermetically sealed case and quality assurance level tx

Semiconductor Material:

Silicon

Voltage Rating In Volts Per Characteristic:

120.0 breakdown voltage, collector-to-base, emitter open and 90.0 breakdown voltage, collector-to-emitter, base open and 7.0 breakdown voltage, emitter-to-base, collector open

Current Rating Per Characteristic:

Between 10.00 amperes source cutoff current and 50.00 amperes source cutoff current

Power Rating Per Characteristic:

140.0 watts small-signal input power, common-collector preset

Maximum Operating Tempurature Per Measurement Point:

200.0 degrees celsius ambient air

Special Features:

Junction pattern arrangement: npn

Test Data Document:

81349-mil-s-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.).

Terminal Type And Quantity:

1 case and 2 pin

Specification Data:

81349-mil-s-19500/528 government specification

Shelf Life:

NI/o

NSN 5961-01-135-2073

Transistor - Page 2 of 2



Demilitarization:

No

Fiig:

A110a0

